Amendments to the Claims

This listing of claims will replace all prior versions and listings of claims in the application:

1-76. (Canceled)

77. (New) A method of maskless lithographic pattern generation using an array of exposure cells wherein the exposure cells expose separate areas of a surface to be exposed.

78. (New) The method of claim 77, wherein a substantial portion of the separate areas are exposed simultaneously.

79. (New) The method of claim 77, further comprising moving through a sequence of horizontal and vertical motions at least one of the array of exposure cells and the surface to be exposed.

80. (New) The method of claim 77, comprising aligning by electro-magnetic coupling the array of exposure cells and the surface to be exposed.

81. (New) The method of claim 77, wherein each exposure cell is selected from the group consisting of a radiation source cell or a shuttered cell.

82. (New) The method of claim 77, wherein the shutter of a shuttered cell is used to vary operation of the exposure cell.

83. (New) The method of claim 77, wherein radiation from a radiation source cell is selected from the group consisting of electrons, protons, X-ray, UV or optical.

84. (New) A method of maskless lithographic pattern generation, the method comprising:

providing an array of exposure cells on a substrate, wherein the exposure cells expose separate areas of a surface to be exposed; and

providing a stress-controlled dielectric layer on the substrate.

85. (New) The method of claim 84, wherein a substantial portion of the separate areas are exposed simultaneously.

86. (New) The method of claim 84, further comprising moving through a sequence of horizontal and vertical motions at least one of the array of exposure cells and the surface to be exposed.

87. (New) The method of claim 84, comprising aligning by electro-magnetic coupling the array of exposure cells and the surface to be exposed.

88. (New) The method of claim 84, wherein each exposure cell is selected from the group consisting of a radiation source cell or a shuttered cell.

89. (New) The method of claim 84, wherein the shutter of a shuttered cell is used to vary operation of the exposure cell.

90. (New) The method of claim 84, wherein radiation from a radiation source cell is selected from the group consisting of electrons, protons, X-ray, UV or optical.

91. (New) The method of claim 84, wherein the stress of the stress-controlled dielectric layer is less than about 8×10^8 dynes/cm^2.